



N-channel Enhancement Mode Mosfet

CX4060

DESCRIPTION

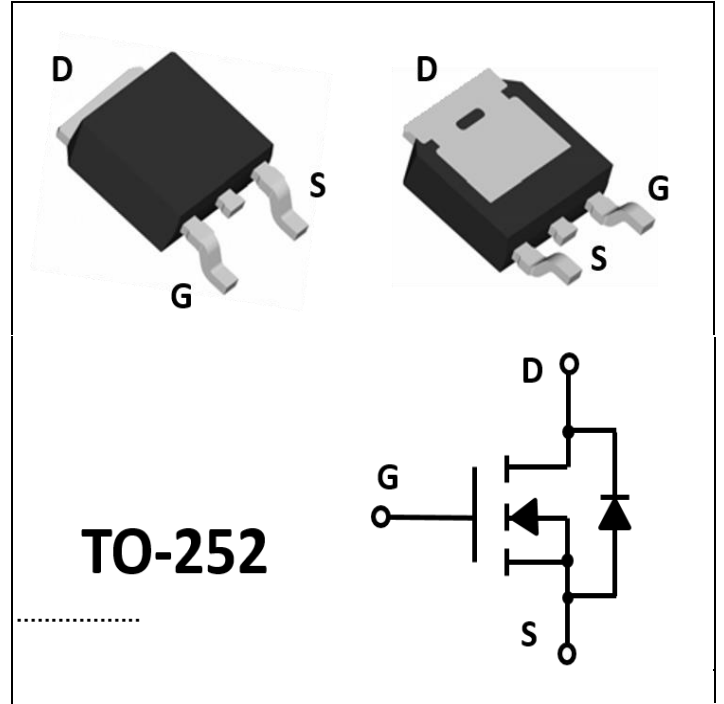
The CX4060 uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. This device is suitable for use as a load switch or in PWM applications.

GENERAL FEATURES

- 40V,60A
 $R_{DS(ON)} < 7m\Omega @ V_{GS} = 10V$
 $R_{DS(ON)} < 12m\Omega @ V_{GS} = 4.5V$
- High Power and current handing capability
- Lead free product is acquired
- Surface Mount Package

Application

- PWM applications
- Load switch
- Power management



TO-252

■ Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Max.	Units	
V_{DSS}	Drain-Source Voltage	40	V	
V_{GSS}	Gate-Source Voltage	± 20	V	
I_D	Continuous Drain Current	$T_C = 25^\circ C$	60	A
		$T_C = 100^\circ C$	39	A
I_{DM}	Pulsed Drain Current ^{note1}	240	A	
E_{AS}	Single Pulsed Avalanche Energy ^{note2}	81	mJ	
P_D	Power Dissipation	$T_C = 25^\circ C$	47	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case	3.2	$^\circ C/W$	
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +175	$^\circ C$	